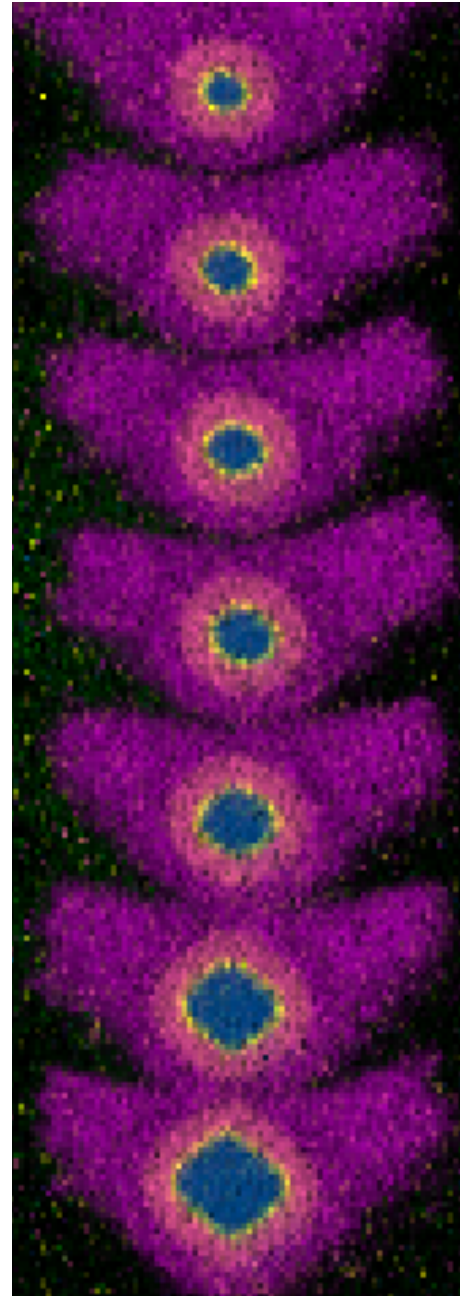
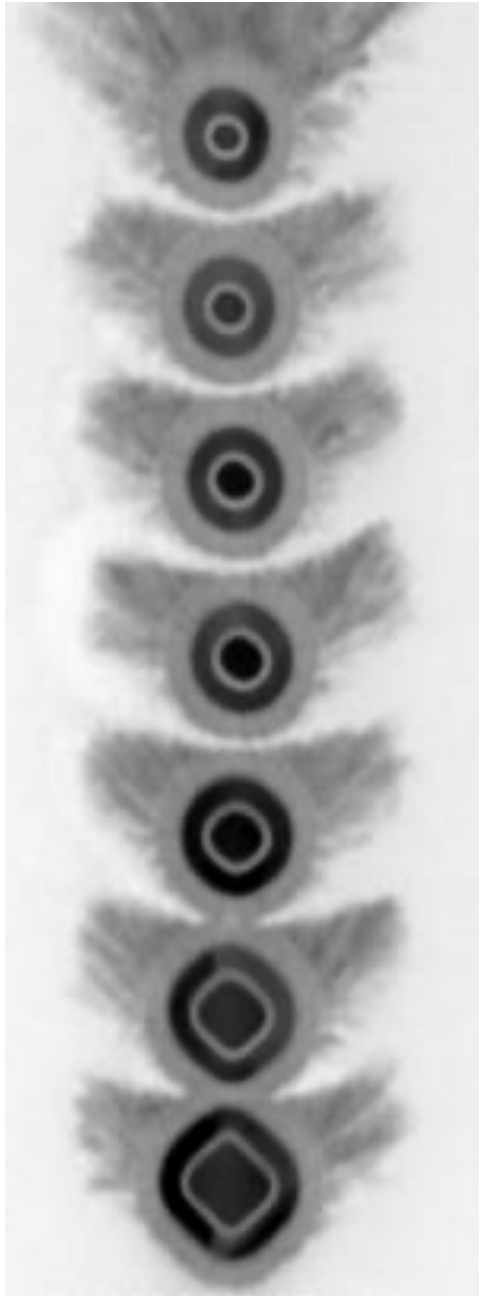


NTU Transistors Highlighted by VLSI and Nature Electronics in 2021



Reference:

(**Highlight paper**) Yi-Chun Liu, Chien-Te Tu, Chung-En Tsai, Yu-Rui Chen, Jyun-Yan Chen, Sun-Rong Jan, Bo-Wei Huang, Shee-Jier Chueh, Chia-Jung Tsen, and **C. W. Liu**, "First Highly Stacked $\text{Ge}_{0.95}\text{Si}_{0.05}$ nGAAFETs with Record $I_{\text{ON}} = 110 \mu\text{A}$ ($4100 \mu\text{A}/\mu\text{m}$) at $V_{\text{OV}}=V_{\text{DS}}=0.5\text{V}$ and High $G_{\text{m,max}} = 340 \mu\text{S}$ ($13000 \mu\text{S}/\mu\text{m}$) at $V_{\text{DS}}=0.5\text{V}$ by Wet Etching," in **Symp. VLSI Technol.**, June 2021, pp. T15-2.

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